

isc N-Channel MOSFET Transistor

2SK1662

DESCRIPTION

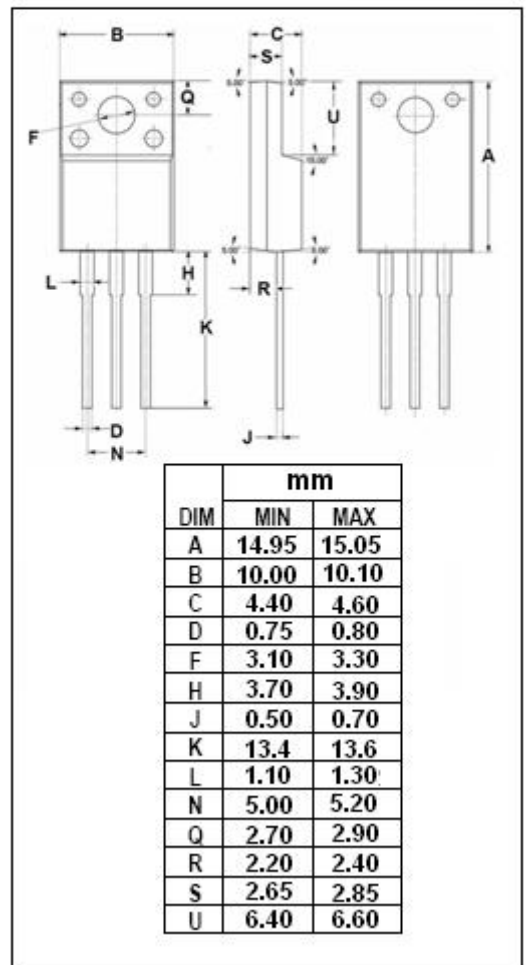
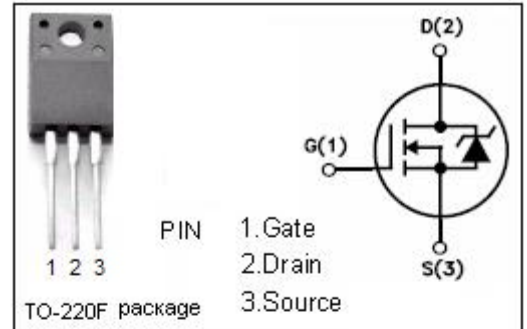
- Drain Current $-I_D = 3A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 700V(\text{Min})$

APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	700	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC = 25^\circ C$	3	A
P_{tot}	Total Dissipation@ $TC = 25^\circ C$	40	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



isc N-Channel Mosfet Transistor**2SK1662****• ELECTRICAL CHARACTERISTICS (T_C=25°C)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0; I _D = 10mA	700			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =10 V _{GS} ; I _D =1mA	2.5		3.5	V
R _{DS(on)}	Drain-Source On-stage Resistance	V _{GS} =10V; I _D =1.5A			5.5	Ω
I _{GSS}	Gate Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0			± 100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =700V; V _{GS} = 0			500	uA